

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1897	((430/320) or (216/27)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/02 09:51
L2	1	10/823939	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2007/07/02 09:20
L3	1	10/823939 and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2007/07/02 09:20
L4	767	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:52
L5	366	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)) with (Angstrom or A)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:22
L6	20	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)) with (Angstrom or A) same ((prior or before or without) near5 (etch\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:52
L7	1	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)) with (Angstrom or A) same ((prior or before) near5 (etch\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:22

## EAST Search History

L8	345	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)) with (Angstrom or A) and ((etch\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:42
L9	2822	((430/320) or (216/27) or (347/56)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/02 09:52
L10	325	L9 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:52
L11	21	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)).clm. with (Angstrom or A).clm. with etch\$4. clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:54
L12	2	L1 and (dielectric or di\$1electric or bi\$1electric or (silicon near oxide) or (silicon near nitride) or (silicon near carbide) or (phosphorous near spin near glass)).clm. with (Angstrom or Ang).clm. with etch\$4.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/07/02 09:54
S1	2	"20050231557"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:11
S2	7	( "2002046266" "0405204" "0456872").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S3	27	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:07

## EAST Search History

S4	288	"347"/\$3 and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:35
S5	176	"347"/\$3 and micro\$fluid\$2 and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:36
S6	55	"347"/\$3 and micro\$fluid\$2 and silicon and (di\$electric\$2 or bi\$electric\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:43
S7	55	"347"/\$3 and micro\$fluid\$2 and silicon and (di\$electric\$2 or bi\$electric\$2) and (angstrom\$1 or A)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:41
S8	103	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:49
S9	58	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:50
S10	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:51
S11	3	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and (pitting or pitted)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:06

## EAST Search History

S12	3	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:02
S13	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and A	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:25
S14	0	("6179401" "6637866" "5850242" "20040113988").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:08
S15	8	("6179401" "6637866" "5850242" "20040113988").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:08
S16	11417	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S17	110	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.) and Lexmark	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S18	9	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.) and Lexmark and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S20	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:23

## EAST Search History

S21	0	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and micro\$fluid\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 07:52
S22	47	"347"/\$3 and di\$electric\$2 with angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:02
S23	3	"347"/\$3 and di\$electric\$2 with angstrom\$1 and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:16
S24	33	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and (ion or etch\$3) and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:25
S25	0	TW0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S26	394544	TW 0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S27	0	TW and 0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37
S28	0	TW and "0405204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37

## EAST Search History

S29	0	TW and "00405204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37
S30	46	CHEN.in. and WU.in. and LUR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40
S31	0	CHEN.in. and WU.in. and LUR.in. and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40
S32	27	CHEN.in. and WU.in. and LUR.in. and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40
S33	10	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:41
S34	10	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:49
S35	1554385	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 adn oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:49
S36	8	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 09:42

## EAST Search History

S37	0	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide and root same mean same square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:51
S38	123667	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide (pit or pitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:52
S39	0	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide and (pit or pitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:52
S40	21	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 09:48
S41	3	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and oxide and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:02
S42	3	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:02
S43	1775	micro\$fluid\$2 and silicon and etch\$3 and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:03
S44	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163"),pn. and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:08

## EAST Search History

S45	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:08
S46	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:10
S47	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3) and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:10
S48	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:15
S49	6	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate and (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:20
S50	5	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate same (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:26



## EAST Search History

S51	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon with (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:16
S52	98	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39
S53	26	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) same root near1 mean near1 square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:38
S54	1	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) same root near1 mean near1 square and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39
S55	1	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square and microfluid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39
S56	4	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:40
S57	254	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:42
S58	44	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and micro\$fluid\$2 and ink\$jet\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:42

## EAST Search History

S59	6	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) with (root near1 mean near1 square) and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:27
S60	5	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) with (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:43
S61	207	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1 or uneven or surface) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:47
S62	19	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:08
S63	24	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1 or uneven or pore\$1 or porous) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:48
S64	2	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and depth same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:09
S65	12	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (depth or deep or thick or thickness) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:22

## EAST Search History

S66	12	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (depth or deep or thick or thickness or holes or hole) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:30
S67	13	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (pitting or pitted or pits or pit or depth or deep or thick or thickness or holes or hole) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:32
S68	1	S67 not S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:32
S69	1	ink\$jet\$4 with silicon and di\$electric and micro\$fluid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 15:12
S70	23	ink\$jet\$4 with silicon and (path\$1 or channel\$1) and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 15:13
S71	2	"6183067".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/02/01 13:30
S72	1495	347/56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/02/01 13:30

## EAST Search History

S74	5	"6402308"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/02/01 13:58
S75	23	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:18
S76	1922	(deep near reactive near ion near etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:18
S77	116	(deep near reactive near ion near etch\$3) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:19
S78	44	((deep near reactive near ion near etch\$3) with silicon) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:20
S79	9	((deep near reactive near ion near etch\$3) with silicon) and Angstrom\$1 and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:20
S80	37	((deep near reactive near ion near etch\$3) with silicon) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 11:12
S81	36105	((deep near reactive near ion near etch\$3) with silicon) and (dielectric or (free near pitted) or (mean near square near depth)) "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:34

## EAST Search History

S82	8	((deep near reactive near ion near etch\$3) with silicon) and (dielectric or (free near pitted) or (mean near square near depth)) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:34
S83	9	((deep near reactive near ion near etch\$3) with silicon) and (di\$electric or (free near pitted) or (root near4 depth)) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:35
S84	9	((deep near reactive near ion near etch\$3) with silicon) and (di\$electric or (free near pit\$4) or (root near4 depth)) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:42
S85	115	((((deep near reactive near ion near etch\$3) or (dry near etch\$3)) with silicon) and (di\$electric or (free near pit\$4) or (root near4 depth)) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 09:46
S86	9	((((deep near reactive near ion near etch\$3) or (dry near etch\$3)) with silicon) and (angstrom with (di\$electric or (free near pit\$4) or (root near4 depth))) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 10:10
S87	1	"5861902".pn. and etch and silicon and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 10:11
S88	1	"5861902".pn. and etch\$3 and silicon and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 11:17
S89	18	((deep near reactive near ion near etch\$3) with (dry near etch\$3) with silicon) and "347"/\$3 not silverbrook.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/09 11:14

## EAST Search History

S90	0	"5861902".pn. and angstorom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 11:17
S91	1	"5861902".pn. and angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:05
S92	2	(root near mean near square near depth) and ((deep near reactive near ion near etch\$3) or (dry near etch\$3)) and (ink or ink\$jet\$4 or jet\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:15
S93	2	(root near mean near square near depth) and ((etch\$3)) and (ink or ink\$jet\$4 or jet\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:14
S94	3	(root near mean near square near depth) and ((etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:14
S95	3	(root near mean near square near depth) and ((deep near reactive near ion near etch\$3) or (dry near etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:19
S96	2	"5861902".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:19
S97	4	("5861902" or "5143577").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:19

## EAST Search History

S98	1	("5861902" or "5143577").pn. and square with mean with root	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/09 12:19
S99	1	10/823939	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/06/19 09:32
S10 0	2	"20020113840"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/06/19 09:43
S10 1	2	"20020113846"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/06/19 09:43
S10 2	2	"5861902".pn. and dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/06/19 09:53
S10 3	1	"5861902".pn. and dielectric and (angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/06/19 09:53
S10 4	1	"5861902".pn. and dielectric same (angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/06/19 09:54
S10 5	56	"347"/\$3 and (dielectric with angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/06/19 09:55

## EAST Search History

S10 6	19	"347"/\$3 and (dielectric with angstrom) same etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/06/19 09:55
S10 7	2	"20020113846"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 12:03
S10 8	2	"5861902".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 12:03
S10 9	483	"347"/\$3 and (etch\$3) and angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/06 12:44
S11 0	48	"347"/\$3 and (etch\$3) and (angstrom with (di\$electric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/06 13:07
S11 1	3	"347"/\$3 and (before with etch\$3) same (angstrom with (di\$electric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/06 13:07
S11 2	3	"347"/\$3 and ((before or prior) with etch\$3) same (angstrom with (di\$electric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/07/06 13:19
S11 3	7795	"347"/\$3 and (etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:12



## EAST Search History

S11 4	1579	"347"/\$3 and (etch\$3) and (Angstrom or A) same (di\$1electric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:12
S11 5	1389	"347"/\$3 and (etch\$3) and (Angstrom or A) same (di\$1electric) and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:13
S11 6	464	"347"/\$3 and (etch\$3) and (Angstrom or A) same (di\$1electric) and silicon and (pitted or pitting or pits or pit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:17
S11 7	1	10/823939	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/10/31 16:18
S11 8	18	"5861902"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 10:58
S11 9	8	"5861902" not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 10:59
S12 0	2	"5861902".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:40
S12 1	35840533	"5861902".pn. and Angstrom\$1 or A	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:40

## EAST Search History

S12 2	1	"5861902".pn. and Angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:47
S12 3	2	"5143577".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:48
S12 4	1269487	"5143577".pn. and print\$3 or jet\$3 or eject\$3 or ink	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:48
S12 5	1	"5143577".pn. and (print\$3 or jet\$3 or eject\$3 or ink)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 11:52
S12 6	0	"347"/\$3 and ((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted) with Angstrom) and ((root near mean near square) or (square near root with average)) same (depth same (pitting or pit\$1 or pitted or crater\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 12:00
S12 7	0	"347"/\$3 and ((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted) same Angstrom) and ((root near mean near square) or (square near root with average)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) same angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 12:03
S12 8	1	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted) same Angstrom) and ((root near mean near square) or (square near root with average)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) same angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 12:05

## EAST Search History

S12 9	1	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted) same Angstrom) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) same angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 12:05
S13 0	4	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted) same (a or Angstrom)) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) same (angstrom or A)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 13:05
S13 1	24	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted)) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 13:06
S13 2	2	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted)) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) and "347"/\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 13:32
S13 3	6	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted)) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1)) and (ink\$jet\$4 or print\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 13:30
S13 4	5	((crater\$1 or smooth or smoothness or (surface near pit\$4) or pitting or pits or pitted)) and ((root with mean with square) or (square with root with average) or (square with root)) same (depth same (pitting or pit\$1 or pitted or crater\$1 or surface)) and "347"/\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/03 13:32

## EAST Search History

S13 5	2055	(surface with (pit\$4 or rough\$4)) same (root with (mean or average) with square)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/08 15:18
S13 6	10	(surface with (pit\$4 or rough\$4)) same (root with (mean or average) with square) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/08 15:26
S13 7	1	(surface with (pit\$4 or rough\$4)) same dielectric same (root with (mean or average) with square) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/08 15:21
S13 8	3	dielectric same (root with (mean or average) with square) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/08 15:21
S13 9	1539589	"20020113846" ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/08 15:26
S14 0	1	"20020113846" ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/11/08 15:27
S14 1	71696	(a or angstrom) with (dielectric near layer\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:29
S14 2	574	(a or angstrom) with (dielectric near layer\$3) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:29

## EAST Search History

S14 3	405	(a or angstrom) near4 (dielectric near layer\$3) and "347"/\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:30
S14 4	218	(a or angstrom) near4 (dielectric near layer\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:32
S14 5	6	(angstrom) near4 (dielectric near layer\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:33
S14 6	1	(angstrom) near4 (dielectric) with (before near etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:34
S14 7	1	(angstrom or A) near4 (dielectric) with (before near etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:34
S14 8	4	(angstrom or A) near4 (dielectric or bielectric or layer) with (before near etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:34
S14 9	4	(angstrom or A) near4 (dielectric or bielectric or layer\$3) with (before near etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:36
S15 0	8	(angstrom or A) near4 (dielectric or bielectric or layer\$3) with ((before or prior) near etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:38

## EAST Search History

S15 1	294	(angstrom or A) near4 (dielectric or bielectric or layer\$3) with (etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:37
S15 2	23	(angstrom) near4 (dielectric or bielectric or layer\$3) with (etch\$3) and "347"/\$3 not silverbrook	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:46
S15 3	154	"347"/\$3 and ((dielectric or insulat\$3 or non\$1conduct\$3) with (surface or material or element or thickness) with Angstrom) or ((dielectric or insulat\$3 or non\$1conduct\$3) with angstrom with ((root near mean) or (root near average) or (square with mean) or (square with average)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 13:06
S15 4	29	"347"/\$3 and ((dielectric or insulat\$3 or non\$1conduct\$3) with (surface or material or element or thickness) with (etch\$3 or engrav\$3) with Angstrom) or ((dielectric or insulat\$3 or non\$1conduct\$3) with angstrom with ((root near mean) or (root near average) or (square with mean) or (square with average)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 13:11
S15 5	1	"347"/\$3 and ((dielectric or insulat\$3 or non\$1conduct\$3) with angstrom with ((root near mean) or (root near average) or (square with mean) or (square with average)) and (pit\$4 or hole or surface) with depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 13:16
S15 6	1	"347"/\$3 and ((dielectric or insulat\$3 or non\$1conduct\$3) with angstrom with ((root near mean) or (root near average) or (square with mean) or (square with average)) and (pit\$4 or hole or surface))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 13:16
S15 7	2	"20020135640"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/14 11:46

## EAST Search History

S15 8	2	"5861902".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/14 12:56
S15 9	2	10/232314	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/14 12:56